

**ABSTRACT**

[0035] An embodiment of the invention reduces damage caused to a polymer ferroelectric layer in a polymer ferroelectric memory device by creating excess holes in the insulating metal nitride and / or metal oxide layers between the metal electrodes and polymer ferroelectric layer. The excess holes in the metal nitride and / or metal oxide trap electrons injected by the metal electrodes under AC bias that would otherwise damage the polymer ferroelectric layer.